

## SCH2411-TL-E-VB Datasheet

### Dual N-Channel 60 V (D-S) MOSFET

#### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) | $Q_g$ (Typ.) |
|--------------|---------------------------|-----------|--------------|
| 60           | 1.200 at $V_{GS} = 10$ V  | 0.3       | 0.75         |
|              | 1.300 at $V_{GS} = 8$ V   | 0.28      |              |
|              | 1.500 at $V_{GS} = 4.5$ V | 0.25      |              |
|              | 1.650 at $V_{GS} = 2.5$ V | 0.15      |              |

#### FEATURES

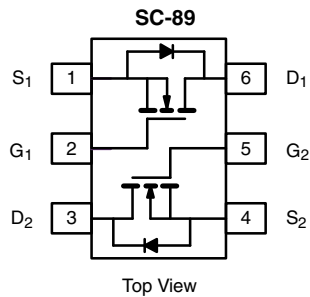
- Trench Power MOSFET
- 100 %  $R_g$  Tested



**RoHS**  
COMPLIANT

#### APPLICATIONS

- Load/Power Switching for Portable Devices
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

| Parameter   |                        | Symbol                            | Limit                | Unit |
|---|------------------------|-----------------------------------|----------------------|------|
| Drain-Source Voltage  |                        | V <sub>DS</sub>                   | 60                   | V    |
| Gate-Source Voltage   |                        | V <sub>GS</sub>                   | ± 12                 |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup> | T <sub>A</sub> = 25 °C | I <sub>D</sub>                    | 0.30 <sup>a, b</sup> | A    |
|   | T <sub>A</sub> = 70 °C |                                   | 0.25 <sup>a, b</sup> |      |
| Pulsed Drain Current  |                        | I <sub>DM</sub>                   | 2                    |      |
| Continuous Source-Drain Diode Current                           | T <sub>A</sub> = 25 °C | I <sub>S</sub>                    | 0.18 <sup>a, b</sup> | A    |
| Maximum Power Dissipation <sup>a</sup>                          | T <sub>A</sub> = 25 °C | P <sub>D</sub>                    | 0.22 <sup>a, b</sup> | W    |
|   | T <sub>A</sub> = 70 °C |                                   | 0.14 <sup>a, b</sup> |      |
| Operating Junction and Storage Temperature Range                |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150          | °C   |

#### THERMAL RESISTANCE RATINGS

| Parameter                                | Symbol     | Typ. | Max. | Unit               |
|--|------------|------|------|--------------------|
| Maximum Junction-to-Ambient <sup>b</sup> | $R_{thJA}$ | 470  | 565  | $^\circ\text{C/W}$ |
|  |            | 560  | 675  |                    |

Notes:

a. Surface mounted on 1" x 1" FR4 board.

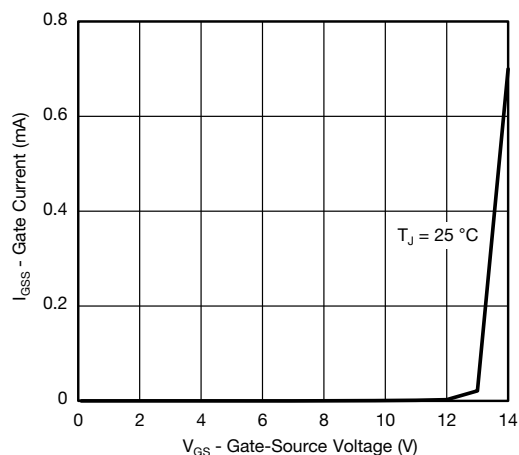
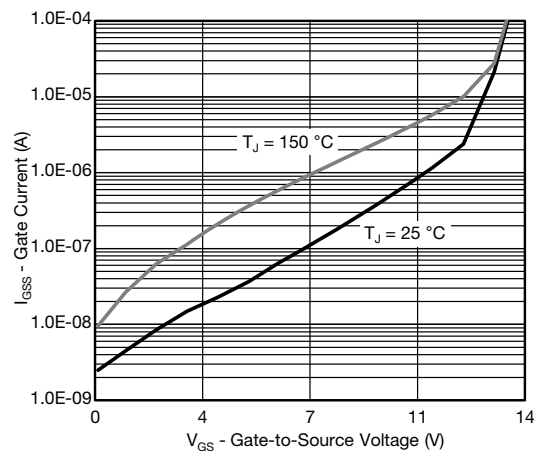
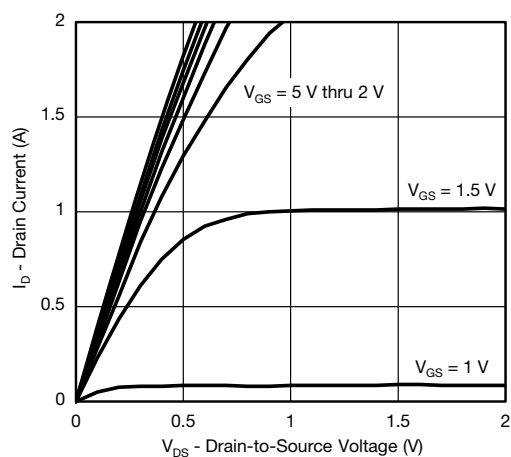
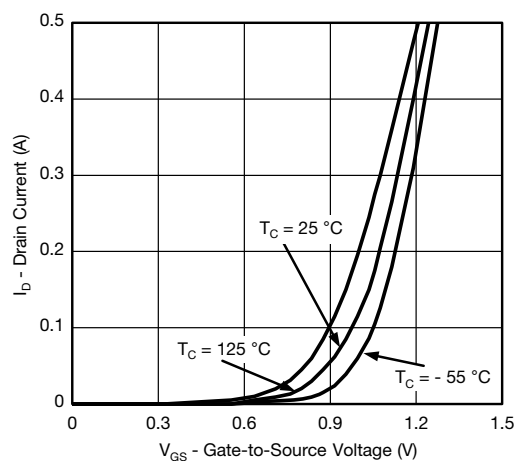
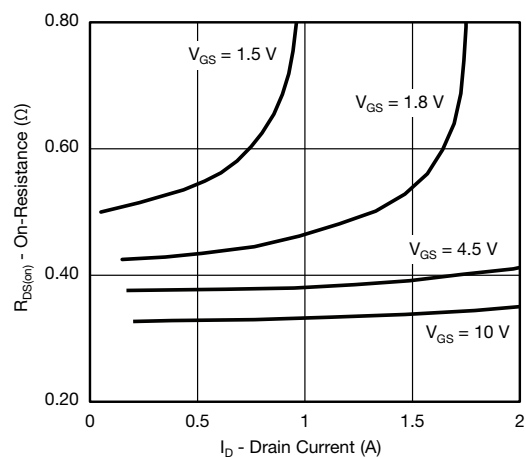
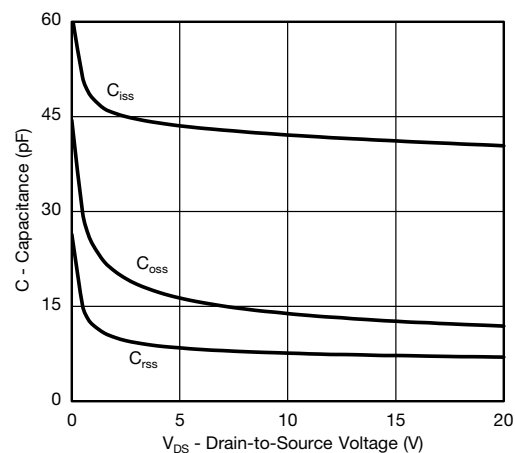
b.  $t = 5$  s.

| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                                      |   |      |       |      |       |
|---|--------------------------------------|---|------|-------|------|-------|
| Parameter   | Symbol                               | Test Conditions   | Min. | Typ.  | Max. | Unit  |
| Static  |                                      |   |      |       |      |       |
| Drain-Source Breakdown Voltage                                  | V <sub>DS</sub>                      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA  | 60   |       |      | V     |
| V <sub>DS</sub> Temperature Coefficient                         | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = 250 μA   |      | 17    |      | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient                     | ΔV <sub>GS(th)</sub> /T <sub>J</sub> |   |      | - 1.8 |      |       |
| Gate-Source Threshold Voltage                                   | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA   |      | 1.6   |      | V     |
| Gate-Source Leakage   | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V  |      |       | ± 30 | μA    |
|   |                                      | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 4.5 V  |      |       | ± 1  |       |
| Zero Gate Voltage Drain Current                                 | I <sub>DSS</sub>                     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V   |      |       | 1    |       |
|   |                                      | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C   |      |       | 3    |       |
| On-State Drain Current <sup>a</sup>                             | I <sub>D(on)</sub>                   | V <sub>DS</sub> = ≥ 5 V, V <sub>GS</sub> = 4.5 V  | 2    |       |      | A     |
| Drain-Source On-State Resistance <sup>a</sup>                   | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.3A   |      | 1.200 |      | Ω     |
|   |                                      | V <sub>GS</sub> = 8 V, I <sub>D</sub> = 0.2 A   |      | 1.300 |      |       |
|   |                                      | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.2 A   |      | 1.500 |      |       |
|   |                                      | V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.15A   |      | 1.650 |      |       |
| Forward Transconductance  | g <sub>fs</sub>                      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 A  |      | 7.5   |      | S     |
| Dynamic <sup>b</sup>  |                                      |   |      |       |      |       |
| Input Capacitance   | C <sub>iss</sub>                     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz  |      | 40    |      | pF    |
| Output Capacitance  | C <sub>oss</sub>                     |   |      | 14    |      |       |
| Reverse Transfer Capacitance                                    | C <sub>rss</sub>                     |   |      | 8     |      |       |
| Total Gate Charge   | Q <sub>g</sub>                       | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 8 V, I <sub>D</sub> = 0.6 A   |      | 1.3   | 2    | nC    |
|   |                                      | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.6 A   |      | 0.75  | 1.2  |       |
| Gate-Source Charge  | Q <sub>gs</sub>                      |   |      | 0.15  |      |       |
| Gate-Drain Charge   | Q <sub>gd</sub>                      |   |      | 0.13  |      |       |
| Gate Resistance   | R <sub>g</sub>                       | f = 1 MHz   | 2.4  | 12.2  | 24.4 | Ω     |
| Turn-On Delay Time  | t <sub>d(on)</sub>                   | V <sub>DD</sub> = 10 V, R <sub>L</sub> = 20 Ω<br>I <sub>D</sub> ≅ 0.5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω |      | 11    | 20   | ns    |
| Rise Time   | t <sub>r</sub>                       |   |      | 16    | 24   |       |
| Turn-Off Delay Time   | t <sub>d(off)</sub>                  |   |      | 26    | 39   |       |
| Fall Time   | t <sub>f</sub>                       |   |      | 11    | 20   |       |
| Drain-Source Body Diode Characteristics                         |                                      |   |      |       |      |       |
| Pulse Diode Forward Current <sup>a</sup>                        | I <sub>SM</sub>                      |   |      |       | 2    | A     |
| Body Diode Voltage  | V <sub>SD</sub>                      | I <sub>S</sub> = 0.5 A  |      | 0.8   | 1.2  | V     |
| Body Diode Reverse Recovery Time                                | t <sub>rr</sub>                      | I <sub>F</sub> = 0.5 A, di/dt = 100 A/μs  |      | 10    | 15   | ns    |
| Body Diode Reverse Recovery Charge                              | Q <sub>rr</sub>                      |   |      | 2     | 4    | nC    |
| Reverse Recovery Fall Time                                      | t <sub>a</sub>                       |   |      | 5     |      | ns    |
| Reverse Recovery Rise Time                                      | t <sub>b</sub>                       |   |      | 5     |      |       |

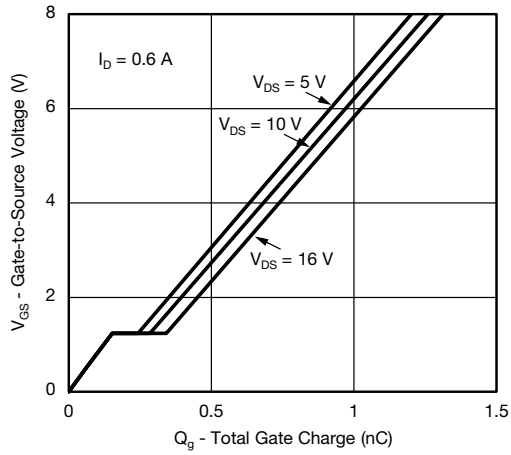
Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

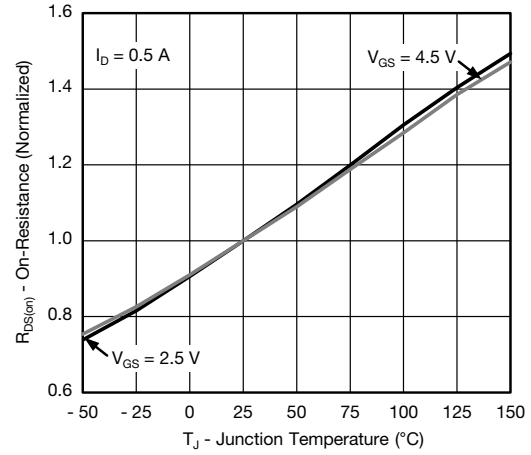
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Gate Current vs. Gate-Source Voltage**

**Gate Current vs. Gate-Source Voltage**

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

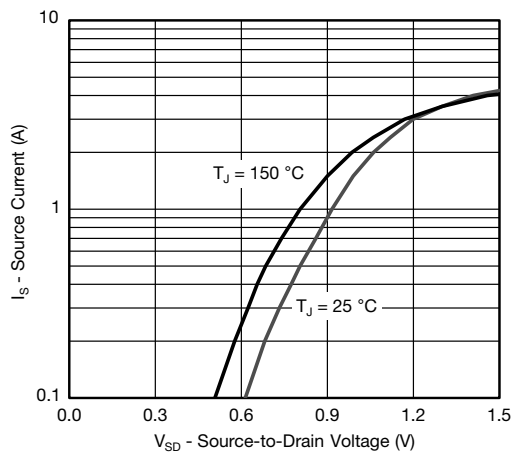
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



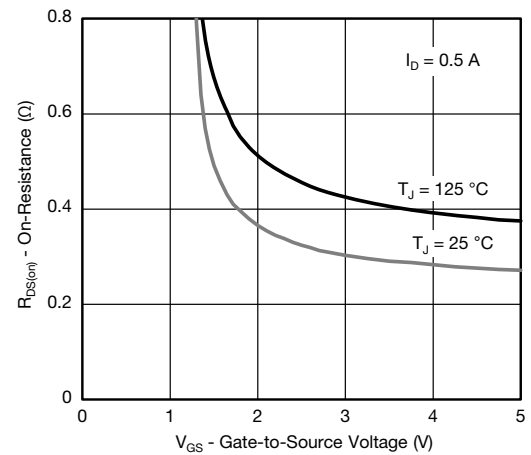
Gate Charge



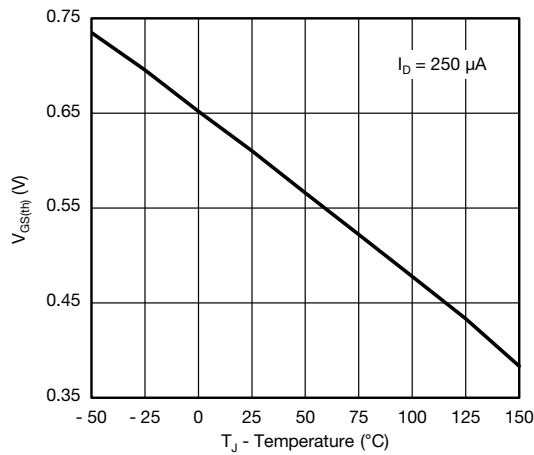
On-Resistance vs. Junction Temperature



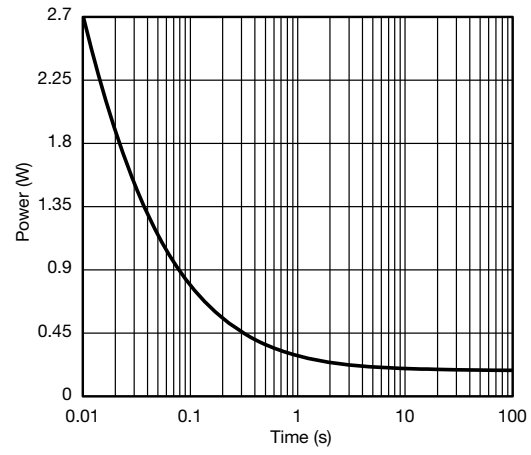
Source-Drain Diode Forward Voltage



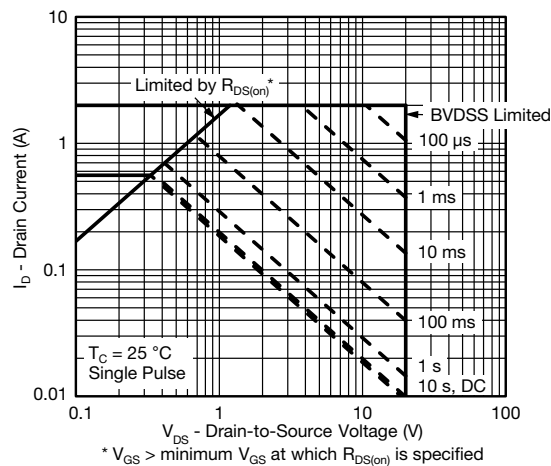
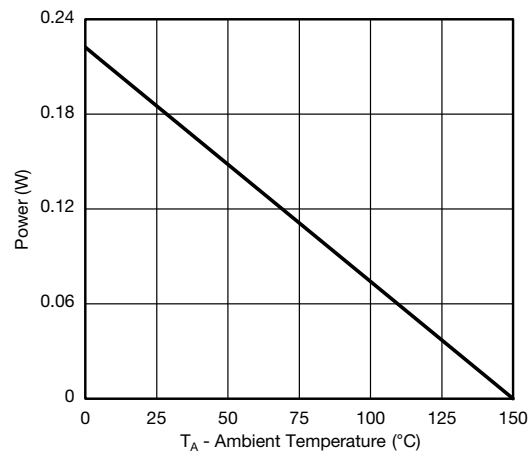
On-Resistance vs. Gate-to-Source Voltage



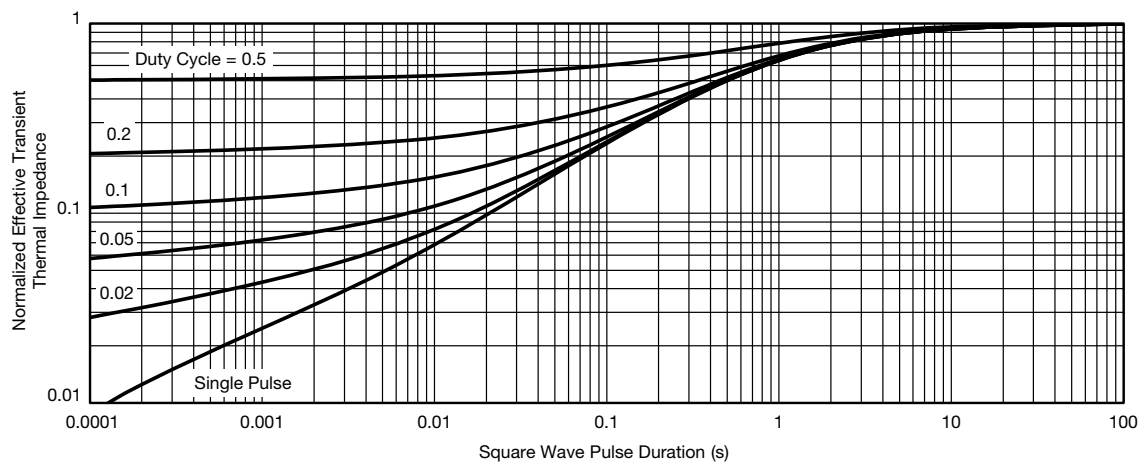
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Safe Operating Area, Junction-to-Ambient**

**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.


**Normalized Thermal Transient Impedance, Junction-to-Ambient**

服务热线：400-655-8788

## RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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